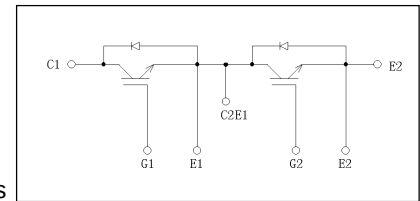


2MBI600U2E-060



IGBT Module U-Series 600V / 600A 2 in one-package

Equivalent Circuit Schematic



Features

- High speed switching
- Voltage drive
- Low inductance module structure

Applications

- Inverter for Motor drive
- AC and DC Servo drive amplifier
- Uninterruptible power supply
- Industrial machines, such as Welding machines

Maximum ratings and characteristics

Absolute maximum ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Item		Symbol	Conditions	Rating	Unit
Collector-Emitter voltage		V _{CES}		650	V
Gate-Emitter voltage		V _{GES}		±20	V
Collector current		I _c	Continuous	600	A
		I _{cp}	1ms	1200	
		-I _c		600	
		-I _c pulse		1200	
Collector Power Dissipation		P _c	1 device	2400	W
Junction temperature		T _j		+150	°C
Storage temperature		T _{stg}		-40 to +125	
Isolation voltage	between terminal and copper base *1	V _{iso}	AC:1min.	2500	VAC
Screw Torque		Mounting *2		3.5	N·m
		Terminals *2		4.5	

*1 : All terminals should be connected together when isolation test will be done.

*2 : Recommendable value : Mounting 2.5 to 3.5N·m(M5 or M6), Terminal 3.5 to 4.5 N·m(M6)

Electrical characteristics (at $T_j=25^\circ\text{C}$ unless otherwise specified)

Item	Symbols	Conditions		Characteristics			Unit
				Min.	Typ.	Max.	
Zero gate voltage collector current	ICES	VGE=0V, VCE=600V		—	—	3.0	mA
Gate-Emitter leakage current	IGES	VCE=0V, VGE=±20V		—	—	600	nA
Gate-Emitter threshold voltage	VGE(th)	VCE=20V, IC=600mA		6.2	6.7	7.7	V
Collector-Emitter saturation voltage	VCE(sat) (terminal)	VGE=15V, IC=600A	TJ=25°C	—	2.15	2.45	V
			TJ=125°C	—	2.40	—	
	VCE(sat) (chip)		TJ=25°C	—	1.85	—	
			TJ=125°C	—	2.10	—	
Input capacitance	Cies	VCE=10V, VGE=0V, f=1MHz		—	43	—	nF
Turn-on time	ton	VCC=300V IC=600A VGE=±15V		—	0.40	1.20	μs
	tr			—	0.22	0.60	
	tr(i)			—	0.16	—	
Turn-off time	toff	RG= 4.7 Ω		—	0.48	1.20	
	tr			—	0.07	0.45	
Forward on voltage	VF (terminal)	VGE=0V IF=600A	TJ=25°C	—	1.90	2.30	V
			TJ=125°C	—	1.95	—	
	VF (chip)		TJ=25°C	—	1.60	—	
			TJ=125°C	—	1.65	—	
Reverse recovery time	trr	IF=600A		—	—	0.35	μs
Lead resistance, terminal-chip*3	R lead			—	0.45	—	mΩ

*3:Biggest internal terminal resistance among arm.

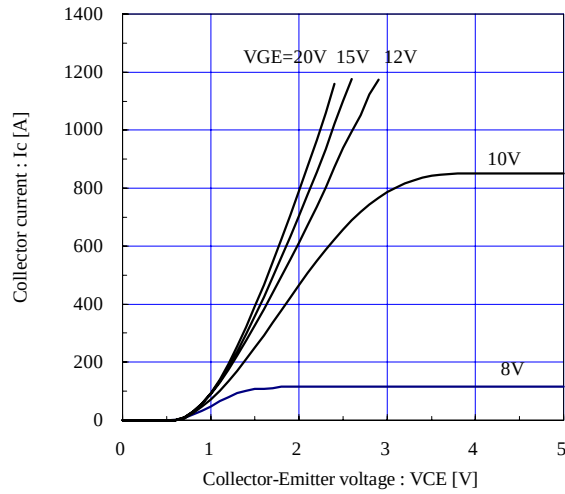
Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance	$R_{th(j-c)}$	IGBT	—	—	0.052	$^\circ\text{C/W}$
	$R_{th(j-c)}$	FWD	—	—	0.086	$^\circ\text{C/W}$
Contact Thermal resistance	$R_{th(c-f)*4}$	With thermal compound	—	0.0167	—	$^\circ\text{C/W}$

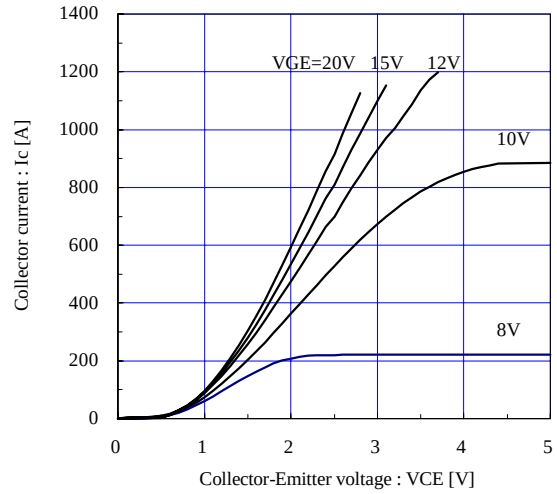
*4 : This is the value which is defined mounting on the additional cooling fin with thermal compound.

Characteristics (Representative)

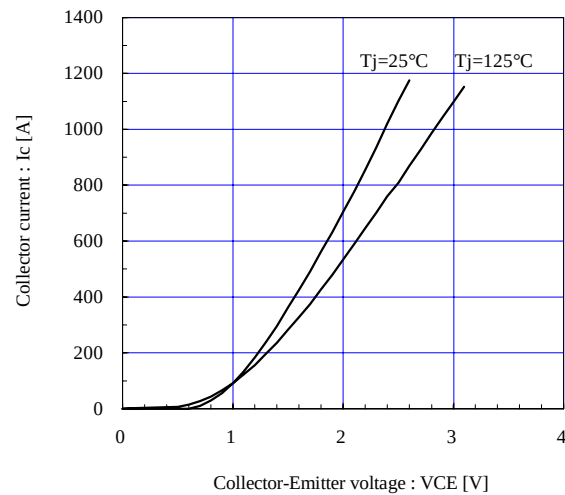
Collector current vs. Collector-Emitter voltage (typ.)
T_j= 25°C / chip



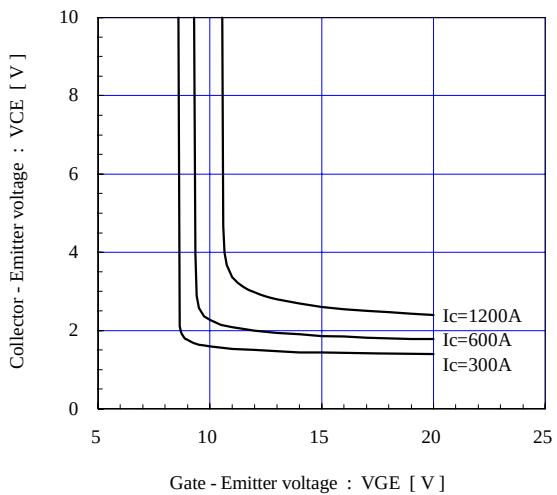
Collector current vs. Collector-Emitter voltage (typ.)
T_j= 125°C / chip



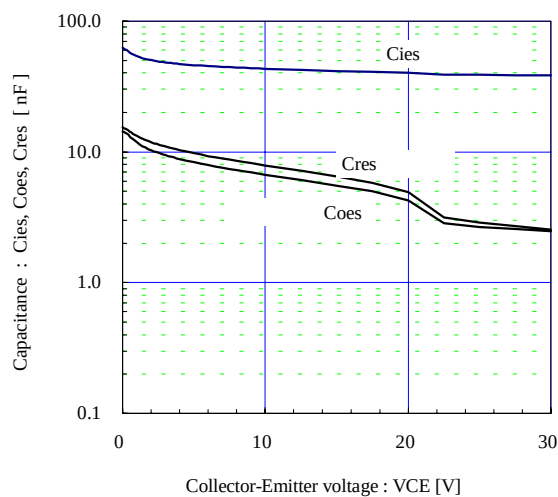
Collector current vs. Collector-Emitter voltage (typ.)
V_{GE}=15V / chip



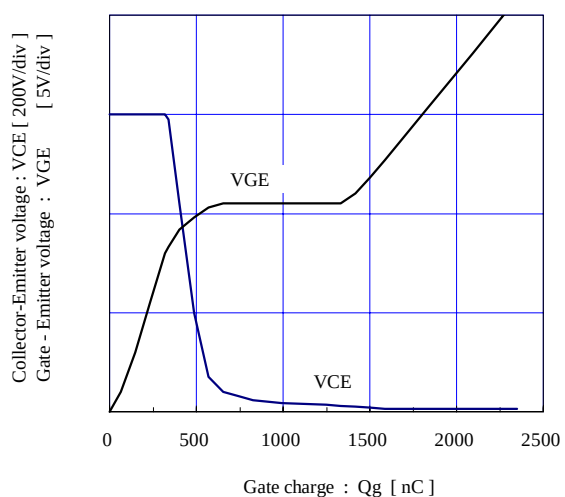
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)
T_j=25°C / chip

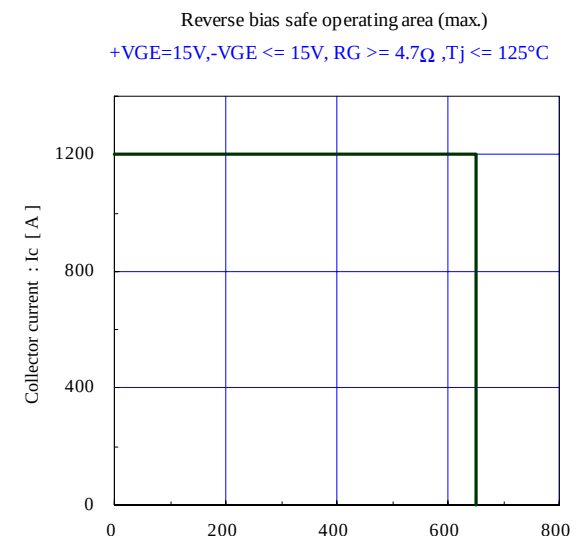
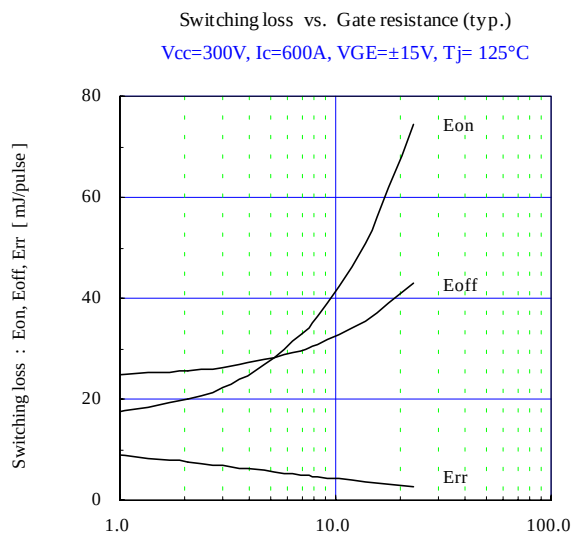
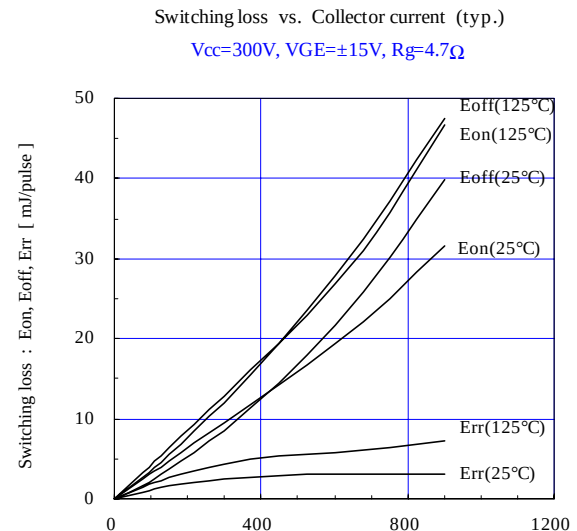
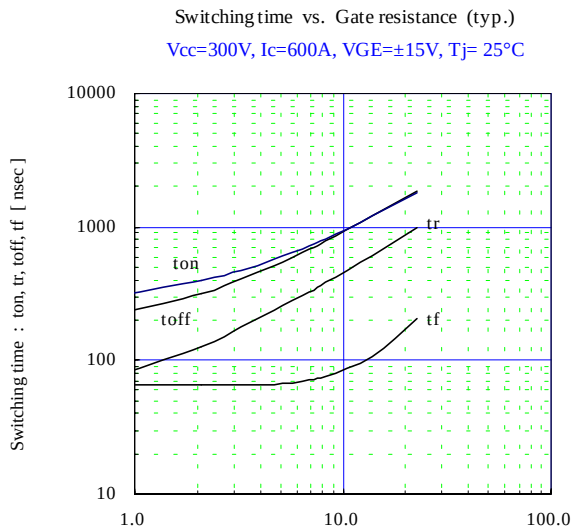
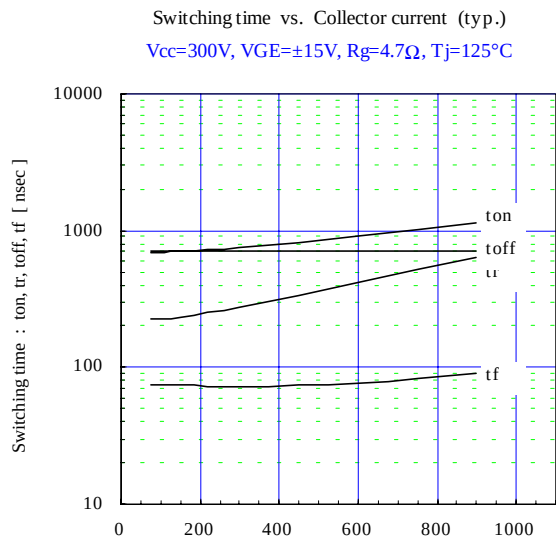
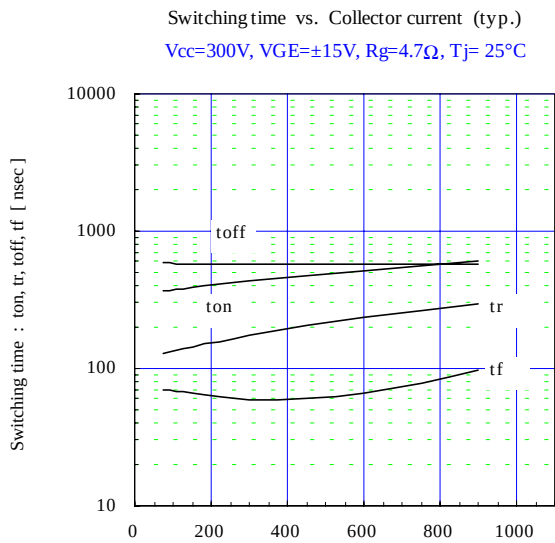


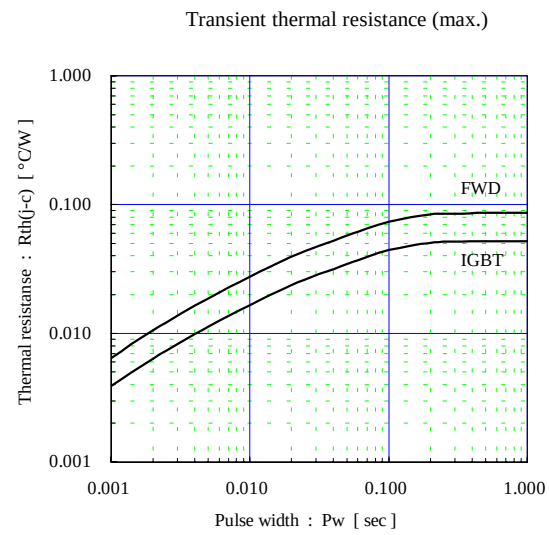
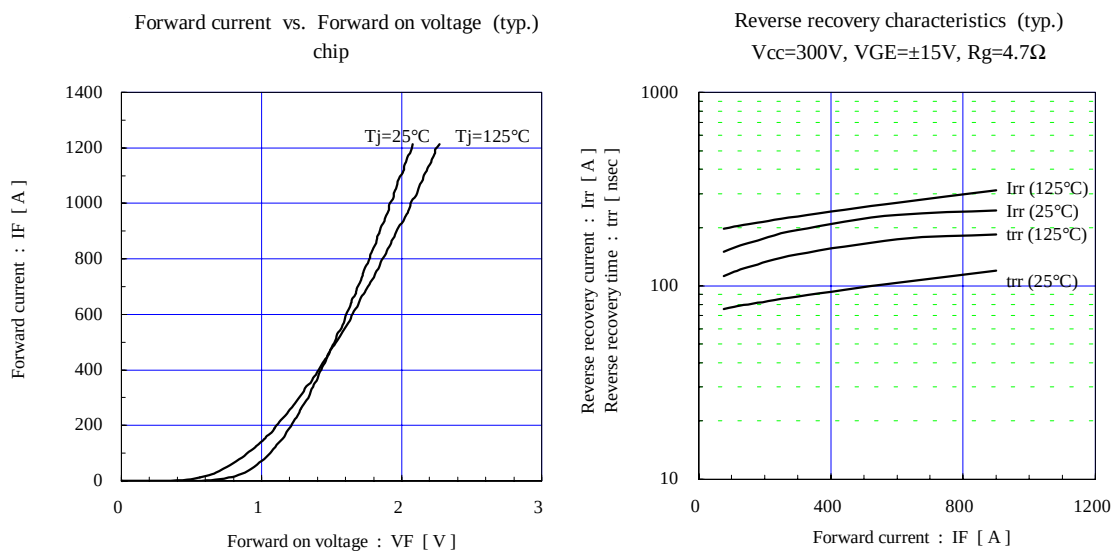
Capacitance vs. Collector-Emitter voltage (typ.)



Dynamic Gate charge (typ.)
V_{CC}=300V, I_c=600A, T_j= 25°C







■ Outline Drawings, mm

M247

